

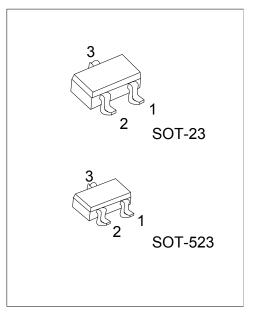
2SA1774

# PNP EPITAXIAL SILICON TRANSISTOR

# **GENERAL PURPOSE** TRANSISTOR

#### **FEATURES**

- \* Excellent h<sub>FE</sub> linearity
- \* Complements the UTC 2SC4617

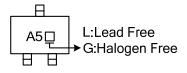


#### **ORDERING INFORMATION**

Ordering Number		Deskare	Pin Assignment			Deeking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
2SA1774L-x-AE3-R	2SA1774G-x-AE3-R	SOT-23	Е	В	С	Tape Reel	
2SA1774L-x-AN3-R	2SA1774G-x-AN3-R	SOT-523	E	В	С	Tape Reel	
Note: Pin Assignment: E: EMITTER B: BASE C: COLLECTOR							

2SA1774L-x-AE3-R	(1)Packing Type (2)Package Type (3)Rank (3)Lead Free	<ol> <li>(1) R: Tape Reel</li> <li>(2) AE3: SOT-23, AN3: SOT-523</li> <li>(3) x: refer to Classification of h<sub>FE</sub></li> <li>(4) G:Halogen Free, L: Lead Free</li> </ol>
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### MARKING



### ■ ABSOLUTE MAXIMUM RATING (T<sub>A</sub>=25°C)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V <sub>CBO</sub>	-60	V
Collector-Emitter Voltage		V <sub>CEO</sub>	-50	V
Emitter-Base Voltage		V <sub>EBO</sub>	-6	V
Collector Current		Ιc	-0.15	Α
Collector Power Dissipation	SOT-23	5	0.22	14/
	SOT-523	Pc	0.15	W
Junction Temperature		ТJ	150	°C
Storage Temperature		T <sub>STG</sub>	-55 ~ +150	°C

Note 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. The device is guaranteed to meet performance specification within  $0^{\circ}$ C ~70°C operating temperature range and assured by design from  $-20^{\circ}$ C ~85°C.

#### ■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C, unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$BV_{CBO}$	I <sub>C</sub> = -50μA	-60			V
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> = -1mA	-50			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	I <sub>E</sub> = -50μA	-6			V
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> = -60V			-0.1	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> = -6V			-0.1	μA
DC Current Transfer Ratio	$h_{FE}$	V <sub>CE</sub> = -6V, I <sub>C</sub> = -1mA	120		560	
Collector-Emitter Saturation Voltage	V <sub>CE (SAT)</sub>	I <sub>C</sub> =-50mA, I <sub>B</sub> =−5mA			-0.5	V
Transition Frequency	f⊤	V <sub>CE</sub> = -12V, I <sub>E</sub> =2mA, f=100MHz		140		MHz
Output Capacitance	C <sub>OB</sub>	V <sub>CB</sub> = -12V, I <sub>E</sub> =0A, f=1MHz		4.0	5.0	pF

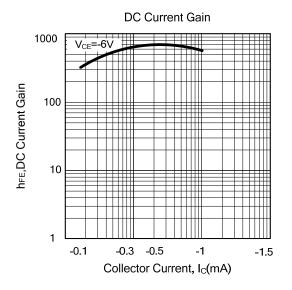
#### CLASSIFICATION OF h<sub>FE1</sub>

RANK	Q	R	S
Range	120 ~ 270	180 ~ 390	270 ~ 560

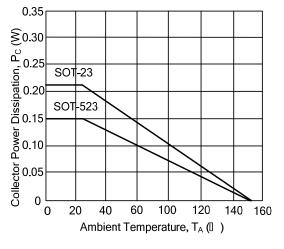


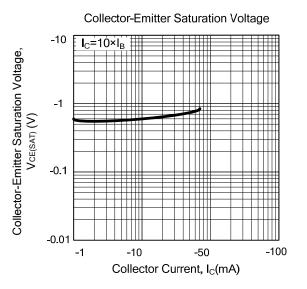
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### TYPICAL CHARACTERISTICS



Collector Power Dissipation vs. Ambient Temperature





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